2SB1132

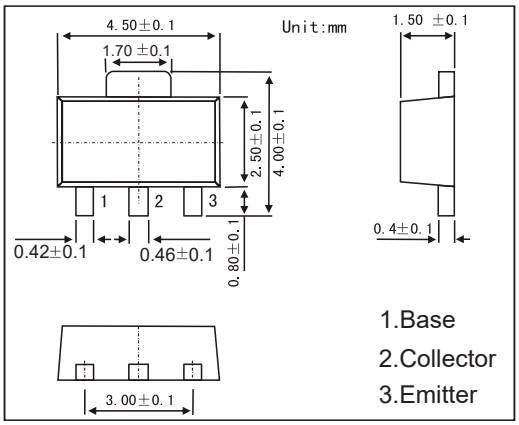
SOT-89 Plastic-Encapsulate Transistors

FEATURES

- Low VCE(sat)
- Compliments to 2SD1664
- PNP Transistors

MECHANICAL DATA

- Case style:SOT-89molded plastic
- Mounting position:any



MAXIMUM RATINGS AND CHARACTERISTICS

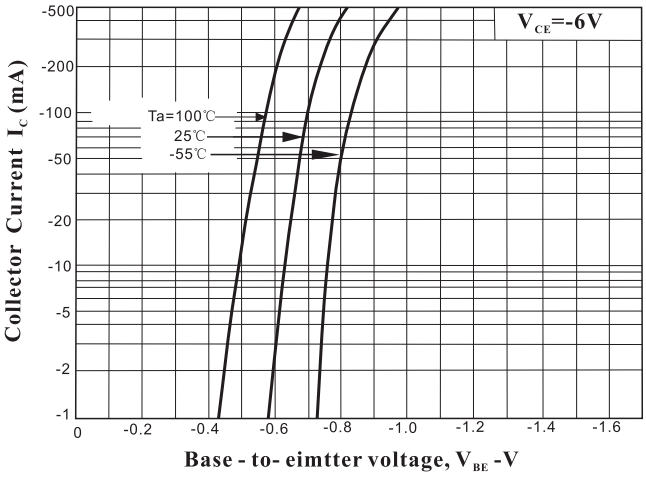
@ 25°C Ambient Temperature (unless otherwise noted)

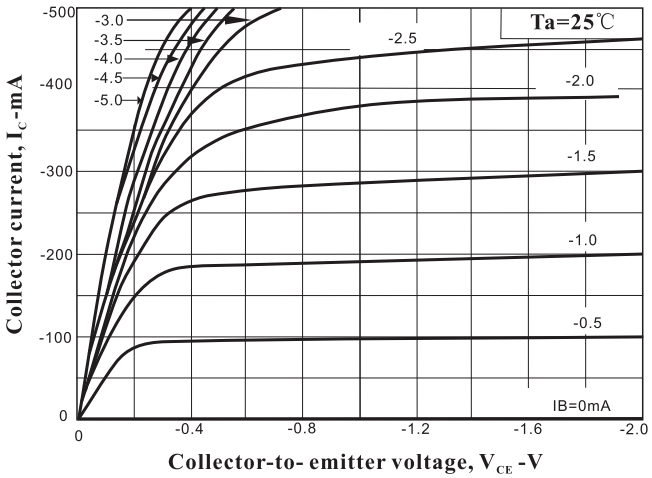
Parameter	Symbol	Rating	Unit
Collector-Base Voltage	VCBO	-40	V
Collector-Emitter Voltage	VCEO	-32	V
Emitter-Base Voltage	VEBO	-5	V
Collector Current (DC)	IC	-1	A
Collector Current Single pulse,	IC	-2	A
Collector Power Dissipation PW=100ms	PC*	0.5	W
Jumction temperature	Tj	150	℃
Storage temperature Range	Tstg	-55 to +150	℃

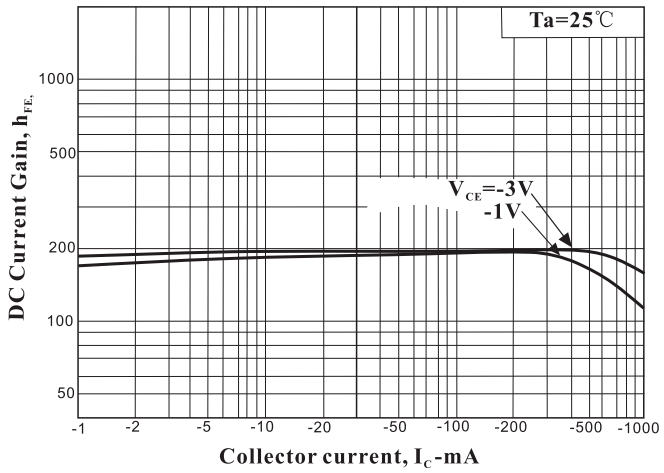
* When mounted on a 40x40x0.7mm ceramic board.

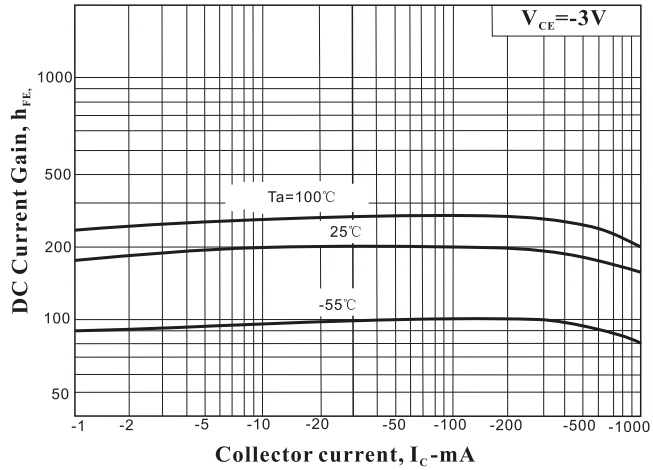
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	VCBO	Ic= -50μA， IE=0	-40			V
Collector- emitter breakdown voltage	VCEO	Ic= -1 mA， IB=0	-32			
Emitter - base breakdown voltage	VEBO	IE= -50μA， IC=0	-5			
Collector-base cut-off current	ICBO	VCB= -20 V , IE=0			-0.5	uA
Emitter cut-off current	IEBO	VEB= -4V , IC=0			-0.5	
Collector-emitter saturation voltage	VCE(sat)	IC=-500 mA, IB=-50mA		-0.2	-0.5	V
DC current gain	hFE	VCE= -3V, IC= -0.1A	82		390	
Collector output capacitance	Cob	VCB= -10V, IE= 0mA,f=1MHz		20	30	pF
Transition frequency	fT	VCE= -5V, IE= 50mA,f=30MHz		150		MHz

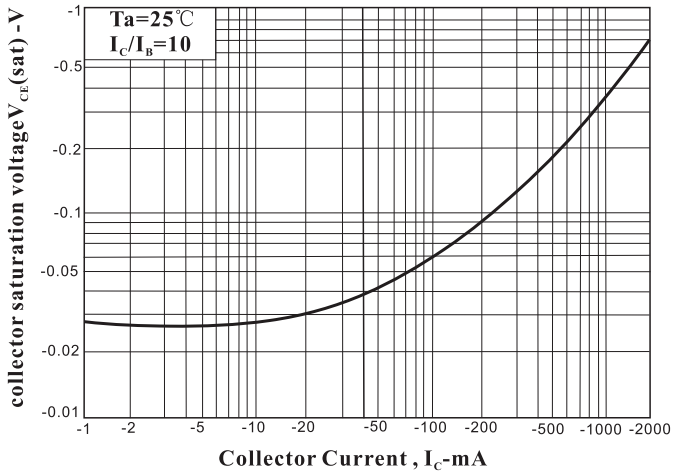
RATINGS AND CHARACTERISTIC CURVES

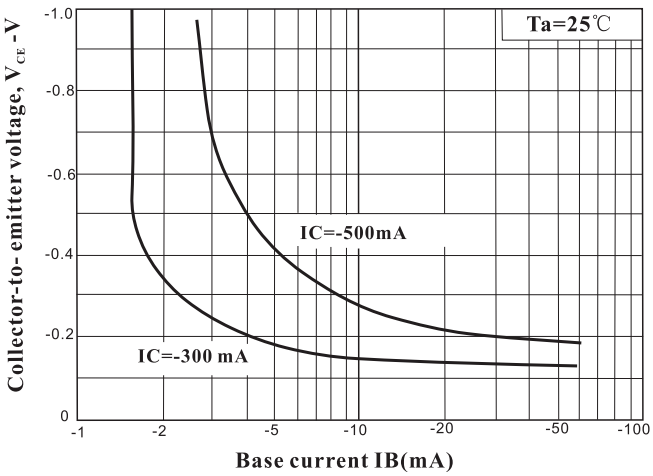












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